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November 2013

# **FQAF13N80**

# N-Channel QFET® MOSFET

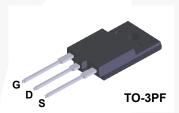
800 V, 8.0 A, 750 m $\Omega$ 

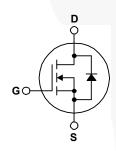
# **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

#### **Features**

- 8.0 A, 800 V,  $R_{DS(on)}$  = 750 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_{D}$  = 4.0 A
- Low Gate Charge (Typ. 68 nC)
- Low Crss (Typ. 30 pF)
- 100% Avalanche Tested





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQAF13N80	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		800	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°	C)	8.0	А	
	- Continuous (T <sub>C</sub> = 100	°C)	5.1	А	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	32	Α	
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	1100	mJ	
I <sub>AR</sub>	Avalanche Current	(Note 1)	8.0	Α	
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	12	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.0	V/ns	
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)		120	W	
	- Derate above 25°C		0.96	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C	

## **Thermal Characteristics**

Symbol	Parameter	FQAF13N80	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.04	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQAF13N80	FQAF13N80	TO-3PF	Tube	N/A	N/A	30 units

# **Electrical Characteristics** T<sub>c</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	racteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	800			V
$\Delta BV_{DSS}$ / $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.95		V/°C
I <sub>DSS</sub>	Zara Cata Valtaga Drain Current	V <sub>DS</sub> = 800 V, V <sub>GS</sub> = 0 V			10	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 640 V, T <sub>C</sub> = 125°C			100	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 4.0 \text{ A}$		0.58	0.75	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 4.0 A		10.5		S
Dynam	ic Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		2700	3500	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		275	360	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			30	39	pF
Switchi	ng Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 400 V, I <sub>D</sub> = 12.6 A,		60	130	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 400 \text{ V}, I_D = 12.0 \text{ A},$ $R_G = 25 \Omega$		150	310	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	1 1 G = 20 32		155	320	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		110	230	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 640 V, I <sub>D</sub> = 12.6 A,		68	88	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		15		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)	/	32		nC
Drain-S	ource Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				8.0	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				36	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 8.0 \text{ A}$			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 12.6 A,		850		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs		11.3	//	μС

- **Notes:** 1. Le sating: Pulse width limited by maximum junction temperature 2. L = 32 mH,  $I_{AS}$  = 8.0 A,  $V_{DD}$  = 50 V,  $R_G$  = 25  $\Omega$ , Starting  $T_J$  = 25°C 3.  $I_{SD} \le 12.6$  A, di/dt  $\le 200$  A/µs,  $V_{DD} \le BV_{DSS}$ , Starting  $T_J$  = 25°C 4. Essentially independent of operating temperature

# **Typical Characteristics**

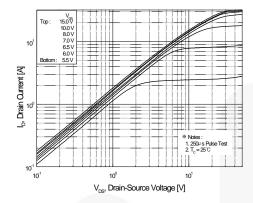
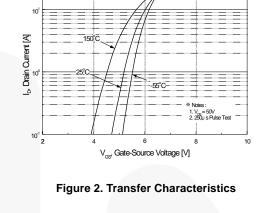


Figure 1. On-Region Characteristics



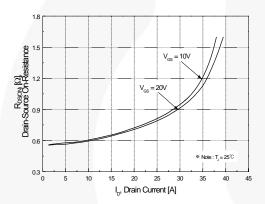


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

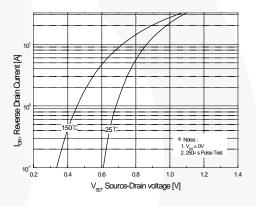


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

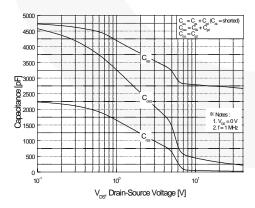


Figure 5. Capacitance Characteristics

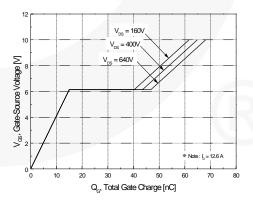


Figure 6. Gate Charge Characteristics

# Typical Characteristics (continued)

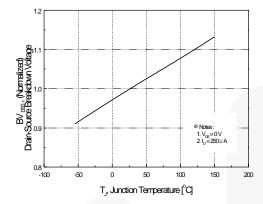


Figure 7. Breakdown Voltage Variation vs Temperature

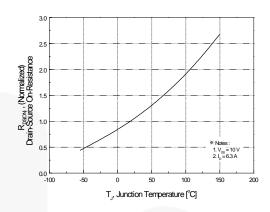


Figure 8. On-Resistance Variation vs Temperature

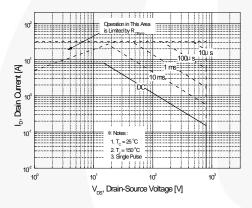


Figure 9. Maximum Safe Operating Area

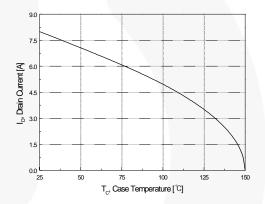


Figure 10. Maximum Drain Current vs Case Temperature

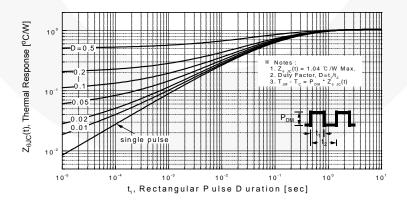


Figure 11. Transient Thermal Response Curve

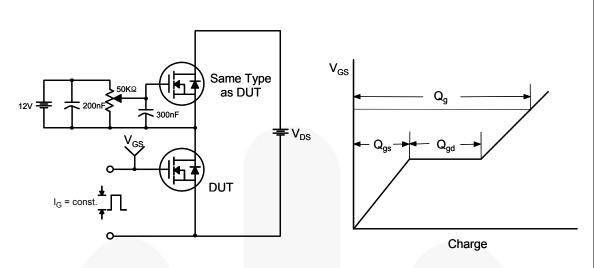


Figure 12. Gate Charge Test Circuit & Waveform

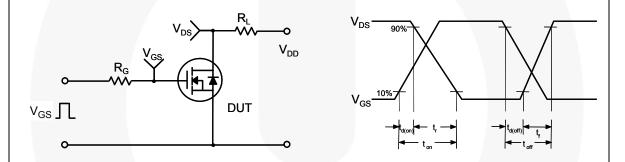


Figure 13. Resistive Switching Test Circuit & Waveforms

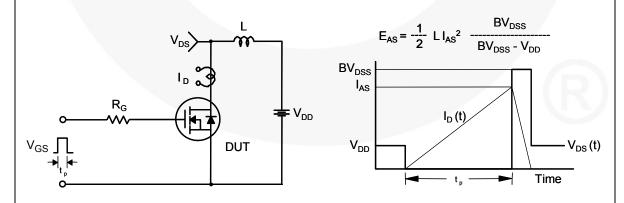
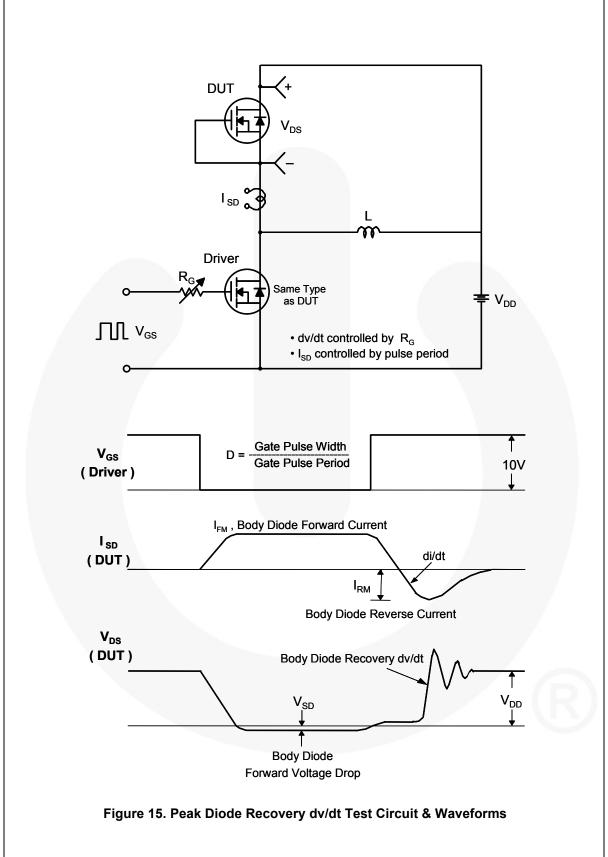


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



## **Mechanical Dimensions**

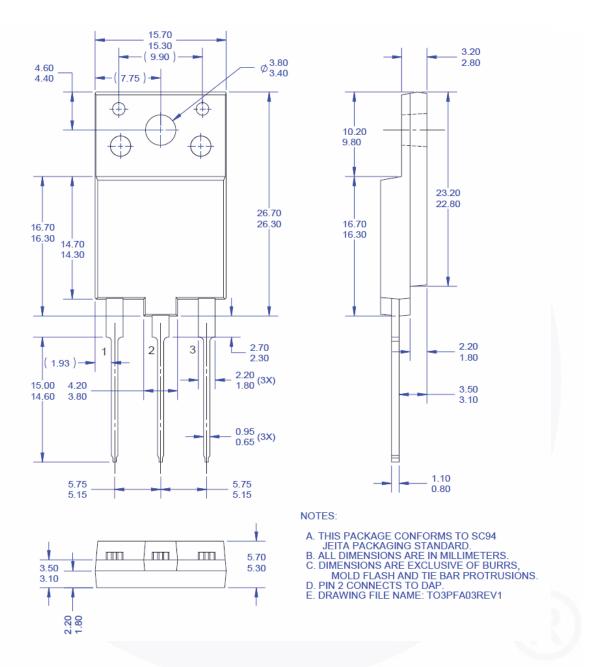


Figure 16. TO3PF, Molded, 3-Lead, Full Pack (AG)

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